

APPENDIX A**MARKED-UP VERSION OF AMENDED CLAIMS**

1. (Amended twice) A method of forming sidewall spacers adjacent opposing vertical sides of a gate electrode, comprising:
 - forming at least one gate electrode over a substrate;
 - forming, at a first temperature in a range of approximately 550°C to 580°C and a first pressure of about 10 mTorr, a first silicon oxide film conformally over the substrate and gate electrode from a combination of gases including bis-(tertiarybutylamino)silane and oxygen;
 - forming, at a second temperature in a range of 580°C to approximately 600°C, a silicon nitride film conformally over the first silicon oxide film from a combination of gases including bis-(tertiarybutylamino)silane; and
 - forming a second silicon oxide film over the silicon nitride film from a combination of gases including bis-(tertiarybutylamino)silane and oxygen.
11. (Amended twice) A method of forming a transistor, comprising:
 - forming at least one gate electrode over a gate dielectric layer, the gate dielectric layer disposed on a substrate;
 - depositing a first silicon oxide film conformally over the substrate and gate electrode from a combination of gases comprising bis-(tertiarybutylamino)silane and oxygen at a temperature of between approximately 550°C and 580°C and a pressure of

about 10 mTorr;

depositing a silicon nitride film conformally over the first silicon oxide film from a combination of gases comprising bis-(tertiarybutylamino)silane and ammonia at a temperature of between 580°C and approximately 600°C;

depositing a second silicon oxide film over the silicon nitride film from a combination of gases comprising bis-(tertiarybutylamino)silane and oxygen; and forming a first sidewall spacer.

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